

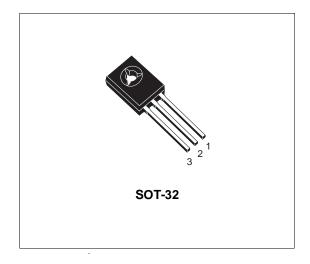
MJE521

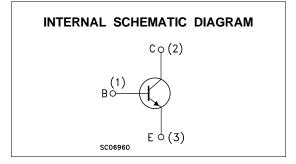
SILICON NPN TRANSISTOR

 STMicroelectronics PREFERRED SALESTYPE

DESCRIPTION

The MJE521 is a silicon Epitaxial-Base NPN transistor in Jedec SOT-32 plastic package. It is intended for use in 5 to 20W audio amplifiers, general purpose amplifier and switching circuits.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage (I _E = 0)	40	V
VCEO	Collector-Emitter Voltage (I _B = 0)	40	V
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	4	V
Ι _C	Collector Current	4	А
Ісм	Collector Peak Current (t _p < 5 ms)	8	А
IB	Base Current	2	А
P _{tot}	Total Dissipation at Tc \leq 25 °C	40	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

September 2003

THERMAL DATA

R _{thj-amb}	Thermal Resistance Junction-ambient	Max	3.12	°C/W	
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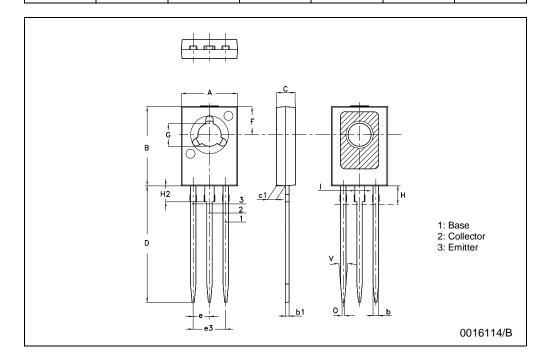
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{СВО}	Collector Cut-off Current (I _E = 0)	V _{CB} = 40 V			100	μA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = 4 V$			100	μA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage $(I_B = 0)$	I _C = 0.1 A	40			V
h _{FE}	DC Current Gain	I _C = 1 A V _{CE} = 1 V	40			

* Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1.5%

DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.425
b	0.7		0.9	0.028		0.035
b1	0.40		0.65	0.015		0.025
С	2.4		2.7	0.094		0.106
c1	1.0		1.3	0.039		0.051
D	15.4		16.0	0.606		0.630
е		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	
I		1.27			0.05	
0		0.3			0.011	
V		10°			10°	

SOT-32 (TO-126) MECHANICAL DATA



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